BLA0912-250R

Avionics LDMOS power transistor Rev. 01 — 3 March 2010

Product data sheet

1. **Product profile**

1.1 General description

Silicon N-channel enhancement mode LDMOS transistor encapsulated in a 2-lead SOT502A flange package with a ceramic cap. The common source is connected to the mounting flange.

Test information

Typical RF performance measured in common source class-AB test circuit at $P_L = 250$ W and 960 MHz to 1215 MHz frequency band. $T_h = 25$ °C; $Z_{th(i-h)} = 0.15$ K/W; unless otherwise specified.

Mode of operation	f	tp	δ	V_{DS}	P_{L}	Gp	$\Delta \mathbf{G_p}$	$\eta_{\textbf{D}}$	P _{droop(pulse)}	t _r	t _f	Z _{th(j-h)}	φins(rel)
	(MHz)	(μs)	%	(V)	(W)	(dB)	(dB)	(%)	(dB)	(ns)	(ns)	(K/W)	(deg)
all modes	960 to 1215	100	10	36	250	13.5	8.0	50	0.1	25	6	0.18	±5
TCAS	1030 to 1090	32	0.1	36	250	14.0	8.0	50	0	25	6	0.07	±5
Mode-S	1030 to 1090	128	2	36	250	13.5	8.0	50	0.1	25	6	0.15	±5
	1030 to 1090	340	1	36	250	13.5	8.0	50	0.2	25	6	0.20	±5
JTIDS	960 to 1215	3300	22	36	200	13.0	1.2	45	0.2	25	6	0.45	±5

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- High power gain
- Easy power control
- Excellent ruggedness
- Source on mounting base eliminates DC isolators, reducing common mode inductance.

1.3 Applications

Avionics transmitter applications in the 960 MHz to 1215 MHz frequency range such as Mode-S, TCAS and JTIDS, DME or TACAN.



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain		
2	gate		<u>, </u>
3	source		2——
			sym039

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packa	Package						
	Name	Description	Version					
BLA0912-250R	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A					

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	75	V
V_{GS}	gate-source voltage		-	±22	V
P _{tot}	total power dissipation	$T_h \le 25$ °C; $t_p = 50~\mu s$; $\delta = 2~\%$	-	700	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$Z_{\text{th(j-h)}}$	transient thermal impedance from junction to heatsink	T _h = 25 °C	<u>[1]</u> 0.18	K/W

^[1] Thermal resistance is determined under RF operating conditions; t_p = 100 μ s, δ = 10 %.

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS} \\$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 3 \text{ mA}$	75	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 300 \text{ mA}$	4	-	5	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 36 \text{ V}$	-	-	1	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GSth} + 9 V;$ $V_{DS} = 10 V$	45	-	-	A
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	1	μΑ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 10 \text{ A}$	-	9	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = 9 \text{ V}; I_D = 10 \text{ A}$	-	60	-	$m\Omega$

Table 7. RF characteristics

RF performance in common source class-AB circuit; $T_h = 25$ °C; $Z_{th} = 0.15$ K/W; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage		-	-	36	V
f	frequency		960	-	1215	MHz
P _L	output power	t_p = 100 μ s; δ = 10 %	250	-		W
Gp	power gain	P _L = 250 W	12	13		dB
η_{D}	drain efficiency	t_p = 100 μ s; δ = 10 %	40	50		%
$Z_{\text{th(j-h)}}$	transient thermal impedance from junction to heatsink	t_p = 100 μ s; δ = 10 %	-	-	0.2	K/W
T _h	heatsink temperature		-55	-	+70	°C
P _{droop(pulse)}	pulse droop power	$t_p = 100 \ \mu s; \ \delta = 10 \ \%$	-	0.1	0.5	dB
$\alpha_{resp(spur)}$	spurious response	VSWR _{load} = 2 : 1	-	-	-60	dBc
t _r	rise time		-	25	50	ns
t _f	fall time		-	6	25	ns

6.1 Ruggedness in class-AB operation

The BLA0912-250R is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 36 V; f = 960 MHz to 1215 MHz at rated load power.

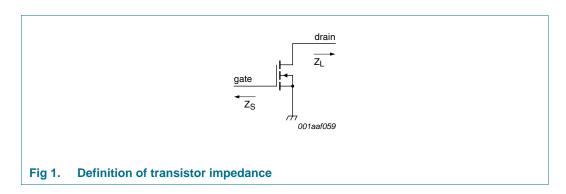
7. Application information

7.1 Impedance information

Table 8. Typical impedance

Typical values per section unless otherwise specified.

f	Z _S	Z _L
MHz	Ω	Ω
960	0.89 - j1.70	1.53 – j1.13
1030	1.37 – j1.23	1.47 – j0.99
1090	2.09 – j1.27	1.38 – j0.85
1140	2.40 - j1.97	1.30 – j0.71
1215	1.51 – j2.61	1.17 – j0.47



7.2 Application circuit

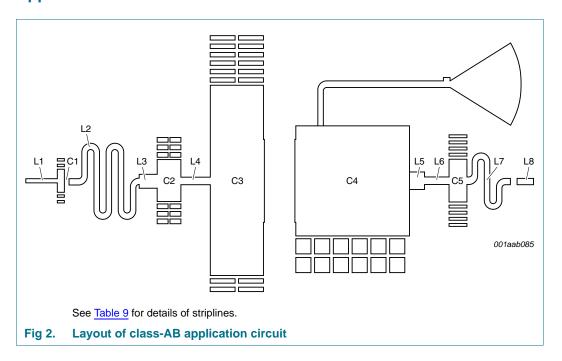


Table 9. Layout details

See Figure 2.

Striplines are on a Rodgers Duroid 6010 Printed-Circuit Board (PCB); $\varepsilon_r = 10.2$ F/m; thickness = 0.64 mm

Component	Description	Dimensions
Input circuit		
L1	stripline	5 mm × 0.8 mm
C1	stripline	1.2 mm × 3.5 mm
L2	stripline	capacitor pad: 1 mm × 1 mm (1×)
		curve: width 0.8 mm; angle 90°; radius 0.8 mm (10×)
		vertical: 3.9 mm \times 0.8 mm (2 \times)
		vertical: 9.4 mm × 0.8 mm (3×)
		horizontal: 0.5 mm × 0.8 mm (4×)
L3	stripline	$3 \text{ mm} \times 2 \text{ mm}$
C2	stripline	4 mm × 6.5 mm
L4	stripline	$5 \text{ mm} \times 1 \text{ mm}$
C3	stripline	8.8 mm \times 30 mm + 0.2 mm \times 13 mm
Output circui	t	
C4	stripline	$0.2~\text{mm} \times 13~\text{mm} + 19~\text{mm} \times 17.1~\text{mm}$
L5	stripline	$2.5~\text{mm} \times 2.3~\text{mm}$
L6	stripline	4 mm × 1 mm
C5	stripline	$3 \text{ mm} \times 6.6 \text{ mm}$
L7	stripline	curve: width 0.8 mm; angle 90°; radius 0.8 mm (6×)
		vertical: 2.2 mm \times 0.8 mm (2 \times)
		vertical: 6 mm \times 0.8 mm (1 \times)
		horizontal: 1 mm \times 0.8 mm (2 \times)
L8	stripline	$2.5~\text{mm} \times 0.8~\text{mm}$
$1/4 \lambda$ line	stripline	curve: width 1 mm; angle 90°; radius 0.8 mm
		vertical: 5 mm × 1 mm
		horizontal: 19 mm × 1 mm

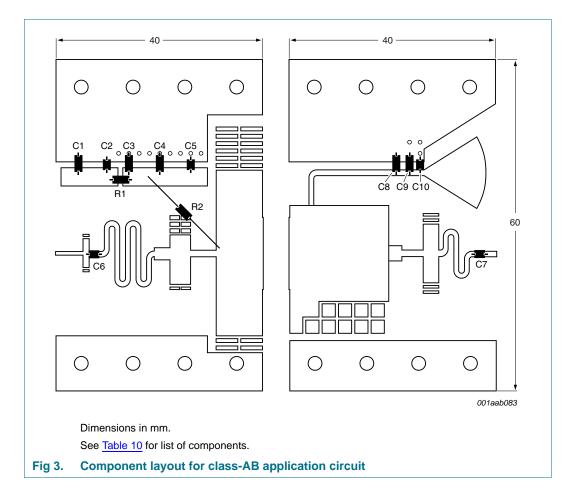


Table 10. List of components See *Figure 3*.

Component	Description	Value		Remarks
C1, C3, C9	multilayer ceramic chip capacitor	1 nF	[1]	
C2, C6, C10	multilayer ceramic chip capacitor	22 pF	[2]	
C4	tantalum SMD capacitor	47 μF		KEMET: T491D476M020AS
C5	multilayer ceramic chip capacitor	56 pF	[2]	
C7	multilayer ceramic chip capacitor	47 pF	[2]	
C8	tantalum SMD capacitor	22 μF		KEMET: T491D226M020AS
R1	SMD resistor	51 Ω		0805
R2	resistor	49.9 Ω		Philips: 2333 156 14999

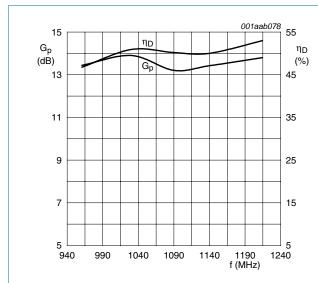
^[1] American Technical Ceramics type 100B or capacitor of same quality.

^[2] American Technical Ceramics type 100A or capacitor of same quality.

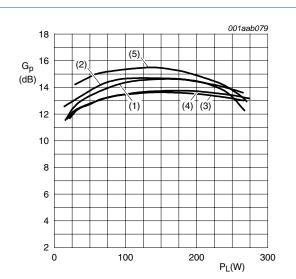
8. Test information

8.1 RF performance

Typical RF performance measured in common source class-AB test circuit at P_L = 250 W and 960 MHz to 1215 MHz frequency band. T_h = 25 °C; $Z_{th(j-h)}$ = 0.15 K/W; unless otherwise specified.



 T_h = 25 °C; V_{DS} = 36 V; I_{Dq} = 150 mA; class-AB; t_{D} = 100 $\mu s; \, \delta$ = 10 %.

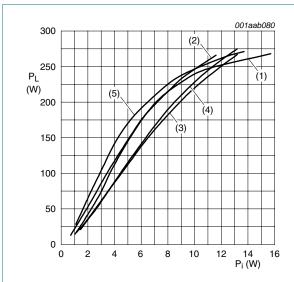


 T_h = 25 °C; V_{DS} = 36 V; I_{Dq} = 150 mA; class-AB; t_p = 100 $\mu s;$ δ = 10 %.

- (1) f = 960 MHz
- (2) f = 1030 MHz
- (3) f = 1090 MHz
- (4) f = 1140 MHz
- (5) f = 1215 MHz

Fig 4. Power gain and drain efficiency as function of frequency; typical values

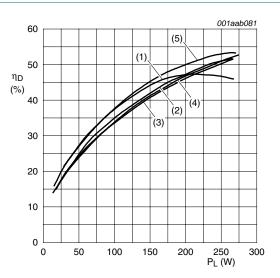
Fig 5. Power gain as a function of load power; typical values



 T_h = 25 °C; V_{DS} = 36 V; I_{Dq} = 150 mA; class-AB; t_p = 100 $\mu s; \, \delta$ = 10 %.

- (1) f = 960 MHz
- (2) f = 1030 MHz
- (3) f = 1090 MHz
- (4) f = 1140 MHz
- (5) f = 1215 MHz

Fig 6. Load power as a function of input power; typical values



 T_h = 25 °C; V_{DS} = 36 V; I_{Dq} = 150 mA; class-AB; t_p = 100 $\mu s;$ δ = 10 %.

- (1) f = 960 MHz
- (2) f = 1030 MHz
- (3) f = 1090 MHz
- (4) f = 1140 MHz
- (5) f = 1215 MHz

Fig 7. Efficiency as a function of load power; typical values

9. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads

SOT502A

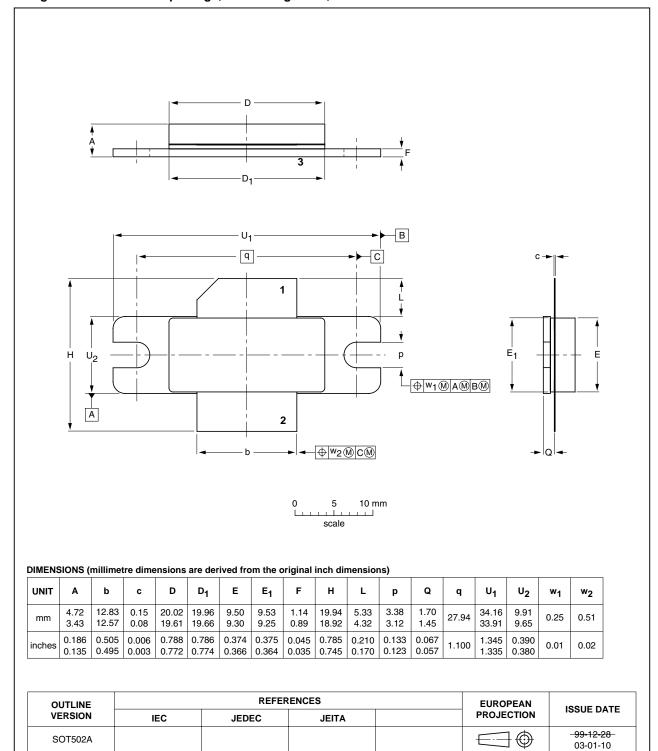


Fig 8. Package outline SOT502A

10. Abbreviations

Table 11. Abbreviations

Acronym	Description
DC	Direct Current
DME	Distance Measuring Equipment
JTIDS	Joint Tactical Information Distribution System
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
Mode-S	Mode Select
RF	Radio Frequency
SMD	Surface Mounted Device
TACAN	TACtical Air Navigation
TCAS	Traffic Collision Avoidance System
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLA0912-250R_1	20100303	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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14. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
2	Pinning information 2
3	Ordering information 2
4	Limiting values
5	Thermal characteristics 2
6	Characteristics 3
6.1	Ruggedness in class-AB operation 3
7	Application information 4
7.1	Impedance information 4
7.2	Application circuit 4
8	Test information 7
8.1	RF performance
9	Package outline 9
10	Abbreviations
11	Revision history
12	Legal information
12.1	Data sheet status
12.2	Definitions11
12.3	Disclaimers
12.4	Trademarks
13	Contact information 12
14	Contents

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